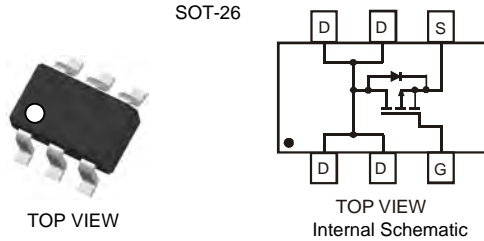


Features

- Low $R_{DS(ON)}$:
 - 80 m Ω @ $V_{GS} = -4.5V$
 - 110 m Ω @ $V_{GS} = -2.7V$
 - 130 m Ω @ $V_{GS} = -2.5V$
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **"Green" Device (Note 4)**

Mechanical Data

- Case: SOT-26
- Case Material – Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 2
- Ordering Information: See page 2
- Weight: 0.008 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	± 12	V
Drain Current (Note 1) Continuous	I_D	$T_A = 25^\circ C$ -3.4 $T_A = 70^\circ C$ -2.7	A
Pulsed Drain Current (Note 2)	I_{DM}	-12	A
Body-Diode Continuous Current (Note 1)	I_S	2.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_D	1.25	W
Thermal Resistance, Junction to Ambient (Note 1); Steady-State	$R_{\theta JA}$	100	$^\circ C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

- Notes:
1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width $t \leq 10s$.
 2. Repetitive Rating, pulse width limited by junction temperature.
 3. No purposefully added lead.
 4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$
Gate-Body Leakage Current	I_{GSS}	—	—	± 100	nA	$V_{DS} = 0\text{V}, V_{GS} = \pm 12\text{V}$
Gate Threshold Voltage	$V_{GS(th)}$	-0.6	—	-1.25	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
On State Drain Current (Note 5)	$I_D(ON)$	-15	—	—	A	$V_{GS} = -4.5\text{V}, V_{DS} = -5\text{V}$
Static Drain-Source On-Resistance (Note 5)	$R_{DS(ON)}$	—	51	80	m Ω	$V_{GS} = -4.5\text{V}, I_D = -4.5\text{A}$
		—	82	110		$V_{GS} = -2.7\text{V}, I_D = -3.8\text{A}$
		—	94	130		$V_{GS} = -2.5\text{V}, I_D = -3.7\text{A}$
Forward Transconductance (Note 5)	g_{FS}	—	6.3	—	S	$V_{DS} = -10\text{V}, I_D = -4.5\text{A}$
Diode Forward Voltage (Note 5)	V_{SD}	—	0.79	-1.26	V	$I_S = -1.7\text{A}, V_{GS} = 0\text{V}$
Maximum Body-Diode Continuous Current (Note 1)	I_S	—	—	1.7	A	—
DYNAMIC PARAMETERS (Note 6)						
Total Gate Charge	Q_g	—	7.3	—	nC	$V_{GS} = -4.5\text{V}, V_{DS} = -10\text{V}, I_D = 4.5\text{A}$
Gate-Source Charge	Q_{gs}	—	2.0	—	nC	$V_{GS} = -4.5\text{V}, V_{DS} = -10\text{V}, I_D = 4.5\text{A}$
Gate-Drain Charge	Q_{gd}	—	1.9	—	nC	$V_{GS} = -4.5\text{V}, V_{DS} = -10\text{V}, I_D = 4.5\text{A}$
Turn-On Delay Time	$t_{D(on)}$	—	12	—	ns	$V_{DS} = -10\text{V}, V_{GS} = -4.5\text{V},$ $R_L = 10\Omega, R_G = 6\Omega$
Turn-On Rise Time	t_r	—	20	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	38	—	ns	
Turn-Off Fall Time	t_f	—	41	—	ns	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Input Capacitance	C_{iss}	—	443	—	pF	
Output Capacitance	C_{oss}	—	125	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	98	—	pF	

Notes: 5. Test pulse width $t = 300\mu\text{s}$.
6. Guaranteed by design. Not subject to production testing.

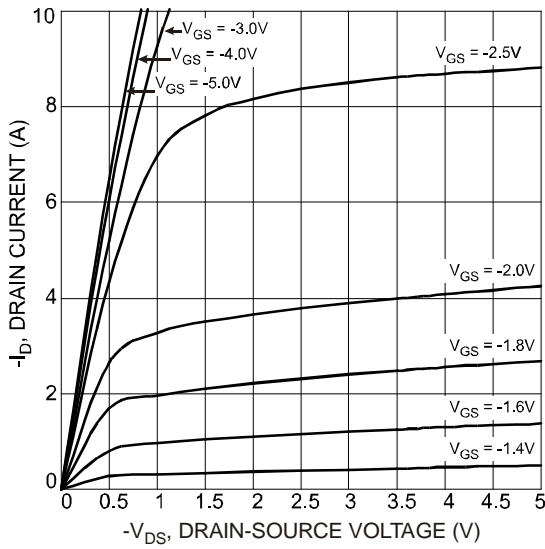


Fig. 1 Typical Output Characteristics

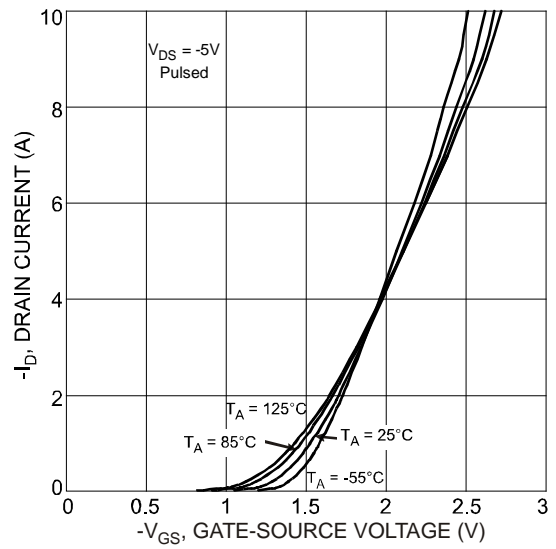


Fig. 2 Typical Transfer Characteristics

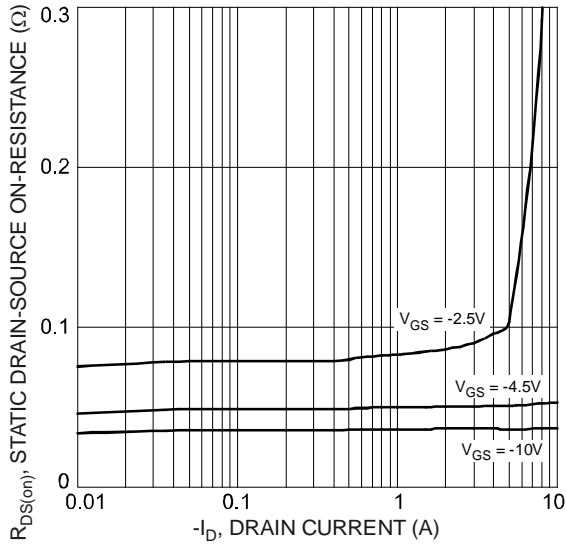


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

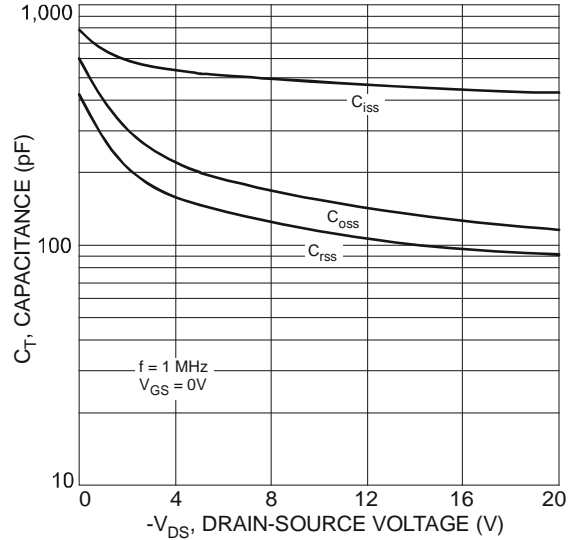


Fig. 4 Typical Total Capacitance

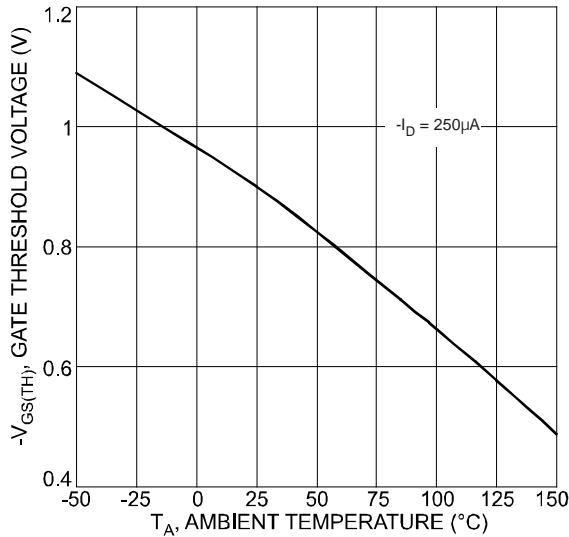


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

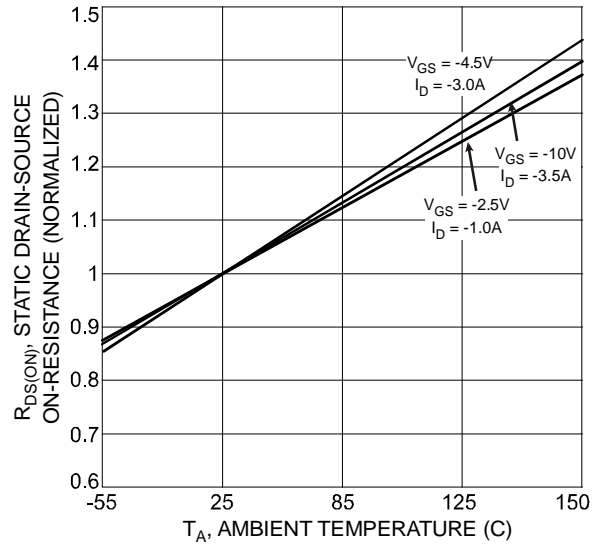


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

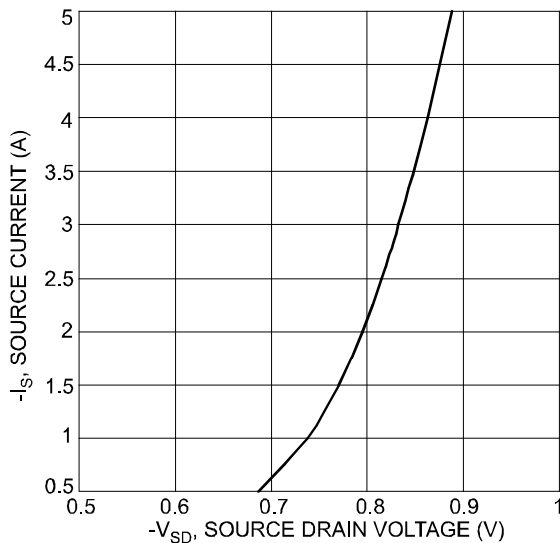


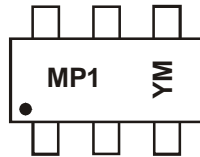
Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Ordering Information (Note 7)

Part Number	Case	Packaging
DMP2130LDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

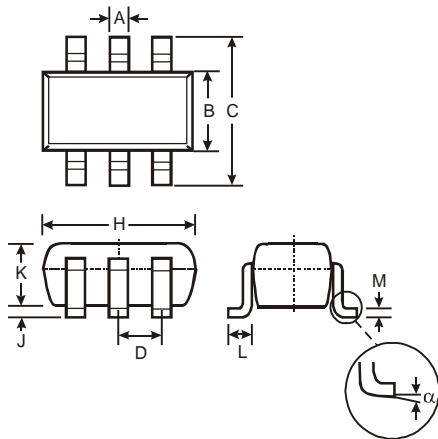


MP1 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: U = 2007
 M = Month ex: 9 = September

Date Code Key

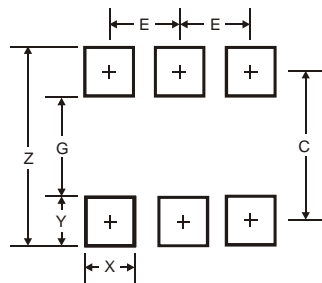
Year	2007			2008			2009			2010			2011		2012
Code	U			V			W			X			Y		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec			
Code	1	2	3	4	5	6	7	8	9	O	N	D			

Package Outline Dimensions



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C	2.40
E	0.95

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